

IN THE CLAIMS

Claims 1-11 (cancelled)

Claim 12 (currently amended): A method to form a RF switch ~~fabricated by a method of~~ by integrating a resistor in circuit with a bottom electrode of a micro-electromechanical switch on a substrate, said method comprising the steps of:

depositing a uniform layer of a resistor material over at least one side of said substrate;

depositing a uniform layer of a hard masked material over said resistor material;

depositing a uniform layer of a metal material over said hard mask material,

wherein said deposited layers form a stack;

patterning and etching a said bottom electrode of said micro-electromechanical switch and resistor lengths from said stack; and

etching said hard mask and metal material from said patterned resistor length to form said RF switch.

Claim 13 (original): The RF switch of Claim 12, wherein said hard mask and metal material remain substantially covering said patterned bottom electrode subsequent to said etching said hard mask and metal material from said patterned resistor length.

Claim 14 (original): The RF switch of Claim 13, further comprising the step of depositing a dielectric over said patterned bottom electrode and resistor following said etching of said hard mask and metal material from said patterned resistor length.

Claim 15 (original): The RF switch of Claim 14, further comprising the step of patterning and etching said deposited dielectric to correspond to said pattern bottom electrode and resistor lengths.

Claim 16 (original): The RF switch of Claim 14, wherein said act of depositing a dielectric is performed immediately subsequent to etching said hard mask and metal material from said patterned resistor length.

Claim 17 (original): The RF switch of Claim 12, wherein said substrate comprises a deposited uniform layer of an anchor material comprising SiO₂.

Claim 18 (original): The RF switch of Claim 12 wherein said resistor material comprises NiCr.

Claim 19 (original): The RF switch of Claim 12, wherein said metal material comprises Al-Si.

Claim 20 (original): The RF switch of Claim 12, wherein at least one of said etching acts comprises wet etching.